

ABSTRACT OF THE DISCLOSURE

A bonded substrate stack formed by bonding first and second substrates is appropriately separated. A first substrate having a porous layer inside and a single-crystal Si layer and insulating layer on the porous layer is brought into tight contact with a second substrate while shifting their central positions to prepare a bonded substrate stack having a projecting portion at which the outer peripheral edge of the first substrate projects outside that of the second substrate. First, a fluid is ejected to the projecting portion to form a separation start portion, and then, separation is started from the separation start portion while rotating the bonded substrate stack.

15

10081068 022102